

INTRODUCE:

HVGT high voltage silicon rectifier diodes is made of high quality silicon wafer chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.

FEATURES:

1. High overload surge capability.
2. High Current,Low Forward Voltage.
3. Avalanche Characteristic.
4. Conform to RoHS and SGS.
5. Epoxy resin molded in vacuumHave anticorrosion in the surface.

APPLICATIONS:

1. High voltage power supply rectifier.
2. High voltage rectifier circuit for microwave oven.
3. Other.

MECHANICAL DATA:

1. Case: epoxy resin molding.
2. Terminal: welding axis.
3. Net weight: 2.10 grams (approx).

SHAPE DISPLAY:

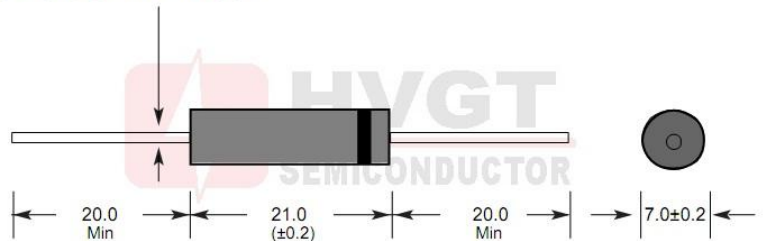


SIZE: (Unit:mm)

HVGT NAME: DO-721

DO-721 Series

Lead Diameter 1.2mm ±0.02



Unit:mm

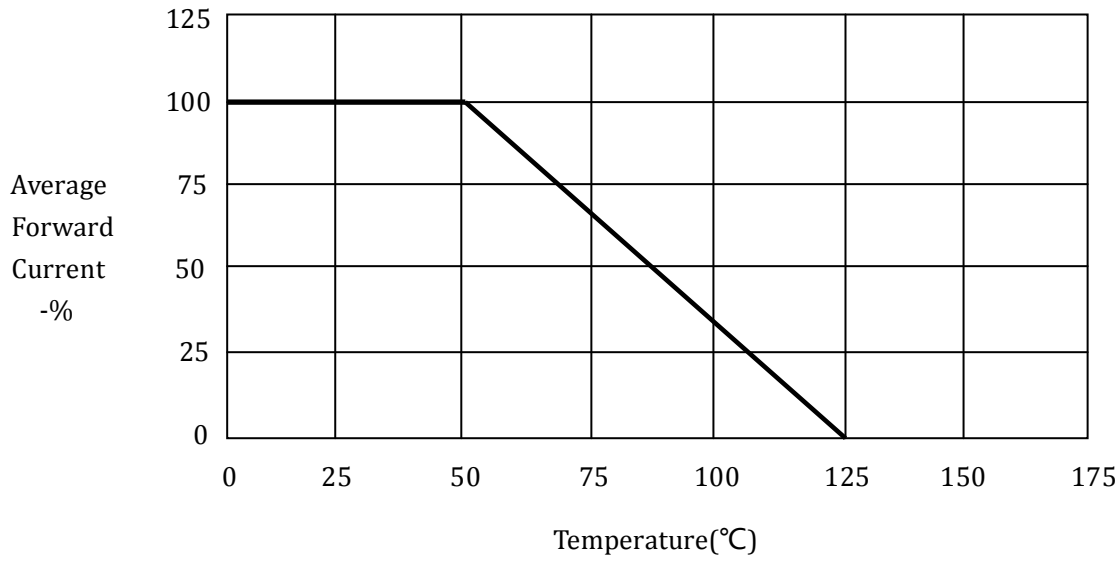
MAXIMUM RATINGS AND CHARACTERISTICS: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	V_{RRM}	$T_A=25^{\circ}C$	12	kV
Non-Repetitive Peak Reverse Voltage	V_{RSM}	$T_A=25^{\circ}C$	14.4	kV
Average Forward Current Maximum	I_{FAVM}	$T_A=50^{\circ}C$	350	mA
		$T_{OIL}=55^{\circ}C$	--	mA
Non-Repetitive Forward Surge Current	I_{FSM}	$T_A=25^{\circ}C$; 50Hz Half-Sine Wave; 8.3ms	30	A
Junction Temperature	T_J		125	$^{\circ}C$
Allowable Operation Case Temperature	T_C		-55~+125	$^{\circ}C$
Storage Temperature	T_{STG}		-55~+175	$^{\circ}C$

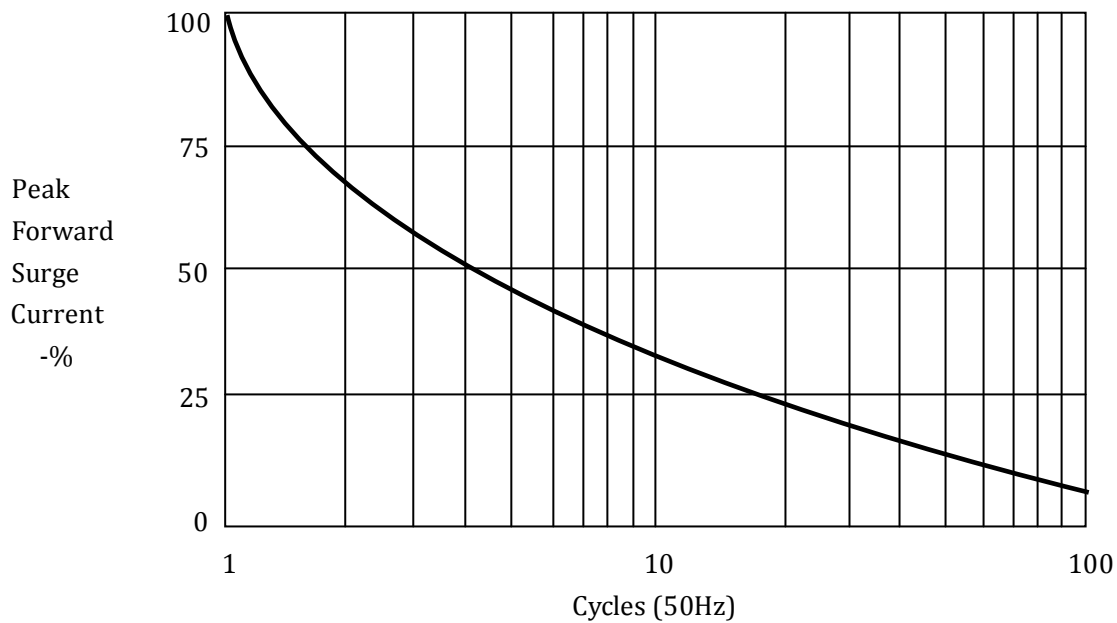
ELECTRICAL CHARACTERISTICS: $T_A=25^{\circ}C$ (Unless Otherwise Specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V_{FM}	at $25^{\circ}C$; at I_{FAVM}	12	V
Maximum Reverse Current	I_{R1}	at $25^{\circ}C$; at V_{RRM}	2.0	μA
	I_{R2}	at $100^{\circ}C$; at V_{RRM}	50	μA
Maximum Reverse Recovery Time	T_{RR}	at $25^{\circ}C$; $I_F=0.5I_R$; $I_R=I_{FAVM}$; $I_{RR}=0.25I_R$	--	nS
Junction Capacitance	C_J	at $25^{\circ}C$; $V_R=0V$; $f=1MHz$	--	pF

Forward Current Derating Curves



Non-Repetitive Surge Current



Marking	Type	Code	Cathode Mark
	HVM12-350	HVM12-350 HVGT	